

SELECTIVE SILICIDE BLOCKING

Abstract of the Disclosure

A selectively silicided semiconductor structure and a method for fabricating same is disclosed herein. The semiconductor structure has silicide present on the polysilicon line between the N+ diffusion or N+ active area and the P+ diffusion or active area at the N+/P+ junction of the polysilicon line, and silicide is not present on the N+ active area and the P+ active area. The presence of this selective silicidation creates a beneficial low-resistance connection between the N+ region of the polysilicon line and the P+ region of the polysilicon line. The absence of silicidation on the N+ and P+ active areas, specifically on the PFET and NFET structures, prevents current leakage associated with the silicidation of devices.